

**LHC1: A semiconductor pixel detector readout chip with internal,
tunable delay providing a binary pattern of selected events**

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Abstract

The Omega3/LHC1 pixel detector readout chip comprises a matrix of 128 x 16 readout cells of 50 μm x 500 μm and peripheral functions with 4 distinct modes of initialization and operation, together more than 800 000 transistors. Each cell contains a complete chain of amplifier, discriminator with adjustable threshold and fast-OR output, a globally adjustable delay with local fine-tuning, coincidence logic and memory. Every cell can be individually addressed for electrical test and masking. First results have been obtained from electrical tests of a chip without detector as well as from source measurements. The electronic noise without detector is $\sim 100 e^-$ rms. The lowest threshold setting is close to 2000 e^- and non-uniformity has been measured to be better than 450 e^- rms at 5 000 e^- threshold. A timewalk of < 10 ns and a precision of < 6 ns rms on a delay of 2 μs have been measured. The results may be improved by further optimization.

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1. Introduction

Pixel detectors are gradually gaining credibility as reliable devices for $\sim 10\ \mu\text{m}$ precision particle detection in high multiplicity, high rate particle physics experiments. At present a 500 000 pixel cell telescope using the Omega2 readout chip bump-bonded to a silicon matrix and comprising 7 planes of $\sim 30\ \text{cm}^2$ each is taking data at CERN in the WA97 heavy ion experiment [1-5]. This operation, successful in most respects, provides lessons for improvements, in particular concerning homogeneity, production yield and testability of the chips. Here we report on the first, to some extent still preliminary results obtained with the improved Omega3/LHC1 chip and hybrid detector assemblies, designed to satisfy the requirements of WA97 and at the same time to explore ways towards future LHC vertex detector requirements.

The choice of binary operation as opposed to full analog readout is adequate for most tracking purposes. It helps to reduce power needs for signal transmission and tends to reduce cell size. The asynchronous operation of the front-end amplifier, latched comparator and tunable delay line reduces the risk of feedthrough of clock signals into the highly sensitive input of the front-end. In this architecture pixel hit data generated after $\sim 150\ \text{ns}$ is stored locally in the delay line and read out for selected events only. This provides low power consumption and minimal traffic on the chip busses. In contradiction with this philosophy, a fast-OR signal is transmitted by every hit to the bottom of the column, using 0-10 μA logic, in order to allow alternative schemes for trigger generation and resolving eventual timing ambiguities. To prevent parasitic signal feedthrough the second level metal layer is used for shielding.

The chip covers a sensitive area of $8\ \text{mm} \times 6.35\ \text{mm}$, just over $0.5\ \text{cm}^2$, with a matrix of 16×127 readout cells, and has a total area of $0.8\ \text{cm}^2$. It has been manufactured in the $1\ \mu\text{m}$ SACMOS process from FASELEC [6], selected because of high component density, equivalent to a $0.6\ \mu\text{m}$ standard CMOS process. We intend to mount 6 chips together onto one detector, called 'ladder', so good die must be identified before assembly and full testing on wafer is foreseen.

The non-uniformity from cell-to-cell of threshold and delay on the previous chip [7,8] was not satisfactory for future LHC applications. The discriminator and delay were redesigned. Timewalk was minimized for good timing resolution and dead time was reduced to avoid loss of hit data. In addition to the cell-to-cell uniformity also the insufficient chip-to-chip uniformity in the WA97 telescope showed the need for individual adjustment of bias supplies per chip. A control chip, the COOP, which also contains an event buffer and zero suppression has been designed [9] for this purpose. In sect. 2 the design of the pixel cell is explained in some detail. The matrix, peripheral logic and modes of operation are discussed in sect. 3. In sect. 4 finally measurement results are presented.

2. Description of the pixel cell

Figure 1 shows layout and photograph of one matrix pixel element, which contains about 400 transistors in an area of $500\ \mu\text{m}$ length by $50\ \mu\text{m}$ width. Fig. 2 shows the corresponding block diagram. The pixel readout chain contains from left to right the successive functions: flip-flop for connection of analog test signal (length $25\ \mu\text{m}$), bump-pad (octagonal in metal 1 and 2 with $22\ \mu\text{m}$ diameter), preamplifier

with leakage current compensation, asynchronous comparator with externally adjustable threshold and fast-OR output (preamp and comparator $\sim 250 \mu\text{m}$), the masking flip-flop ($25 \mu\text{m}$), a globally adjustable delay ($100 \mu\text{m}$) with local 3-bit fine-tuning ($100 \mu\text{m}$), coincidence logic, memory cell ($25 \mu\text{m}$) and bus lines.

The input of each pixel is connected by a solder bump to a corresponding matrix element on the semiconductor detector. Fig. 3 shows a picture of such bumps before connection. The bumps connect to silicon diode detector elements that are also $50 \mu\text{m} \times 500 \mu\text{m}$. On the photograph in fig. 4 of a part of the detector chip one may just distinguish the circular contact opening on the right end of each cell. Dummy cells, at the bottom, connected by thin lines to a guard ring, surround the matrix of active cells. The guard ring is connected to a separate ground on the readout chip. The lowest pixel cell in fig. 4 is connected to the current sensing circuit on the readout chip and provides a compensation current of up to 10 nA for each of the the 127 active cells in the column, i.e. up to $40 \mu\text{A cm}^{-2}$.

The charge preamplifier is based on a folded cascode circuit similar to that in the Omega2 chip and is designed to consume $19 \mu\text{W}$. The feedback capacitance C_{fb} is about 3.5 fF . The feedback resistance is non-linear to limit the swing for high input signals. Following extraction of parasitics and resimulation a source follower was added at the output to improve speed. The signal risetime is designed $\sim 80 \text{ ns}$. An additional reset has been provided to force a fast return to zero to decrease the dead-time of the cell after a large signal.

The comparator (fig. 5) is structurally the same as in Omega2 and is designed to operate at low power, $15 \mu\text{W}$. The current in the bistable nonlinear load determines the threshold and can be varied externally via a common bias adjustment. In the state after reset this current runs in one of the two branches of the non-linear load. A large enough signal will cause the bistable load to change state switching the current to the other side. This change is detected by a fast sensing circuit and latched. Attention was paid to threshold uniformity by symmetric layout of the two branches and the non-linear load and by proper dimensioning of transistors. We used matching data provided by Faselec AG on the SACMOS2 process, extrapolated to the SACMOS1 process.. A tradeoff with timewalk had to be made as a large load transistor improves matching but slows down response by increased capacitance. The reset (together with preamp reset) can be external or from the feedback from the delay chain. The comparator provides a fast-OR and it can be masked, i.e. inhibited to operate if the preamp or the comparator prove to be too noisy or defective. The fast-OR outputs of all cells in a column are connected together in a wired-OR configuration.

The delay chain (fig. 6) is based on current-deprived inverters: 36 stages now instead of 3 in Omega2. This together with the feedback after 4 stages to reset the front-end allows several hit pulses to propagate consecutively in the delay line and should decrease dead-time to below $\sim 250 \text{ ns}$. As distinctive feature a 3-bit digitally controlled delay tuning has been added. This trimming delay contains 3 more inverter stages which can be made current-deprived or not by a switch across the current source, as indicated in fig. 7. A fourth inverter is used to restore a proper edge of the signal before it is used in the subsequent coincidence logic. The coincidence logic will write a one into the data flip-flop if during the externally provided strobe

a rising edge at the end of the delay line is detected. The data flip-flops of all pixels in one column are configured as a shift-register during data readout.

3. Peripheral functions, modes of operation

As mentioned already in the introduction the readout chip LHC1/Omega3 contains a one-sided peripheral region and a matrix of readout cells of 16 columns and 128 rows: 127 active rows, 1 test row at the top, and a row of current sensing cells at the bottom which are connected to dummy sensor cells on the detector, one for each column. A photograph of the complete chip is shown in fig. 8. The chip size is 8.72 mm x 9.12 mm of which 63% is sensitive area. All 16 cells of the test row are permanently connected to the analog test input, contrary to the active pixels, which are optionally connected by digital control of the test flip-flop. This allows to write various test patterns, but it is undesirable to address all cells in the matrix at the same time because there may be excessive load on the power supplies.

The peripheral functions are naturally organized according to the column structure as is clear from fig. 8. Because of the need to butt together several chips on a ladder, only one side, the 'bottom', is used for these peripheral functions. Biases are regenerated here for each column and logic signals are buffered. The wired fast-OR in the column is detected and buffered. On the one hand this signal is used to produce a chip-wide OR, sent off-chip for possible trigger purposes, and which allows to self-generate a strobe for the event data. On the other hand the OR signal of a column is used on-chip as time-stamp to resolve possible ambiguities. If this circuit (fig. 9) is enabled and a hit in the column is detected via a fast-OR, a one is written into a 40 MHz shift register, which corresponds to the LHC bunch-crossing clock frequency. If the length of the shift register is chosen appropriately, taking into account the trigger latency and delay between hit and fast-OR, the output of the shift register can be used as an enable signal for the eventual strobe. The strobe then would not be applied to the pixels if in that column no hit was present in the time slot of interest. This would allow to use a strobe wider than 25 ns in case the delay within each pixel is not sufficiently accurate across the chip. At present the depth of the shift register has been limited to 16, it should be adjusted to 80 or 120 for expected trigger latency times in ATLAS resp. CMS.

The periphery of the chip also contains bidirectional tristate output buffers to read data and to write and read contents of the various registers. Control logic defines the four distinct operation modes selectable via external control lines.

Mode 0 (Omega operation) This 'normal' mode covers also the actual operation in Omega2. During data taking the strobe is connected to all pixels. If a hit of sufficient amplitude has been sensed in one of the pixels within the strobe time, the data flip-flop of that pixel will be set. Readout requires 128 clock pulses to shift out the rows of data after a strobe. One may apply the clock to certain columns only and keep others in data collection mode which allows to determine possible cross-talk during readout.

Mode 1 (LHC operation) Instead of applying the strobe to each column directly, it is enabled by a signal generated on-chip by the fast-OR of the column as described earlier. This allows a wider strobe to be

used while keeping timing ambiguities rare. This facility has been included to cope with LHC timing needs in case of unsatisfactory uniformity of the delays within each pixel.

Mode 2 (Initialize Delay adjust register) and 3 (initialize Test and Mask registers) These initialisation ('slow control') modes allow to read and write the contents of the delay adjust register (3 bits per pixel), and the test and mask registers (twice one bit per pixel).

In both Omega (0) and LHC (1) mode, the delay adjust and external fast-OR output can be enabled or disabled.

4. Timing and threshold measurements

The threshold and timing uniformity are critical parameters of any pixel readout system for particle physics experiments. In recent beam measurements using the Omega2 pixel chip bump-bonded to a 300 μm thick Si detector [5] we have demonstrated that 100% detection efficiency for high energy particles can be obtained if the pixel threshold is set at $\sim 9\,000\text{ e}^-$.

Timewalk

In fig. 10 the timewalk in one pixel cell in the LHC1 chip is shown. This measurement was made on one of the test pixels at the top of the matrix using electrical stimulation. A timewalk of better than 10 ns can be observed for input signals above $\sim 9\,000\text{ e}^-$ for a pixel

threshold at or below $\sim 5\,000\text{ e}^-$. It is to be noted that the optimal biasing of the circuit for lowest possible threshold was not yet achieved for the data reported in the figs. 10 - 15. While a threshold $\sim 2000\text{ e}^-$ has been used already on the full matrix, there are indications that an even lower value is possible but some digital interference may prevent operation of all cells at such low thresholds.

Adjustable delay

While discussing the internal pixel delay lines it was mentioned that these can be adjusted globally. Fig. 11 shows the dependence of the average pixel delay on the bias current I_{dl} . This delay can be adjusted between 1.5 μs and 3 μs . The expected latency time for the level-1 trigger in ATLAS is $\sim 2\text{ }\mu\text{s}$ while in CMS it is 3 μs . The uniformity of this delay determines the minimum strobe duration needed to detect all hits belonging to one event. We expected random effects in CMOS transistor threshold voltages (V_t) to dominate the fluctuations in delay. The critical components were dimensioned to be as large as possible within the limited area available and 36 inverter stages were implemented in the delay chain to minimize these fluctuations. However, as can be observed from fig. 12(a), the measured delay fluctuation across one chip is rather systematic from top to bottom of the chip. A similar, but less pronounced behaviour was observed from left-to-right as well. This systematic variation seems to correlate with a rather pronounced V_t gradient across the wafer. The delay variation for the first evaluated chips is a factor of 2 greater than assumed in the design.

Individual pixel tuning

In order to obtain the timing precision needed in LHC experiments a delay tuning is provided for each pixel individually. It is controlled by the content of a 3-bit register in the pixel which can be addressed externally. The delay correction is done in 2 steps. The range of delay variation is determined and the

delay adjust current, I_{dla} , is adapted to cover this range. Then the appropriate 3-bit code is written into every pixel to implement the individual delay correction. In fig. 12(b) the corrected response time of the pixels on one chip is shown. All pixels respond within a 25 ns window indicating a precision of better than 6 ns rms. This measurement is executed with a uniform, electrical signal. For particle signals timewalk has to be included to obtain actual timing.

Threshold measurements

It was explained how the threshold can be varied as a function of the current I_{th} , which biases the bistable non-linear load of the discriminator. However, there is a certain threshold spread between pixels. In order to quantify this spread and to estimate the noise in the front-end the electrical input signal was varied and the number of positive responses per trigger (expressed as a %) was measured. The curves obtained for the test row are shown in fig. 13. Taking the 50% point in the curves as threshold we can determine an estimate for the threshold variation, be it with low statistics. At this threshold the variation is 450 e^- rms. The difference in input signal between 2 % reponse and 98 % response corresponds to 4σ of the noise distribution. This yields an estimated electronic noise of $\sim 100 e^-$ rms for the test row which is not connected to a sensor element. By increasing the external bias current I_{th} from 5 μA upwards the thresholds are moving nearly linearly up to $\sim 15\,000 e^-$ as illustrated in fig. 14. It has been noticed that there is a systematic top-down gradient and on some chips also a slight left-right gradient in the effective threshold value. These systematic gradients influence in particular the timewalk characteristics and improvements in the performance can be expected if the cause for the gradients can be eliminated.

Calibration of threshold using radioactive sources

In order to calibrate the electrical measurements of threshold and uniformity, a fully assembled readout chip with detector was exposed to radioactive sources with well-defined photon emission lines. These were ^{109}Cd (22 keV and 25 keV), ^{241}Am (60 keV) and ^{57}Co (122 keV). The threshold current, I_{th} , of the chips was varied in small steps and each time the number of photons counted for a fixed number of trigger strobes was recorded for every pixel. When the threshold increases beyond the characteristic photon energy the count rate falls to zero. This allows to determine the threshold current required to obtain a particular threshold on every pixel. As shown in fig. 15 the 3 calibration points could be superimposed to an electrical threshold scan of the same chip. This provides a threshold calibration in absolute energy and in equivalent incident e^- . This allows to determine independently the exact value of the injection capacitance and in this case it was found to be equal to the expected one. In fig. 15 the threshold is again shown to vary linearly between 3 000 e^- and 15 000 e^- . Beyond that the discriminator is still functional, but the threshold sensitivity to I_{th} increases strongly. Using this calibration curve and the data for the ^{241}Am source the threshold variation across the whole chip could be estimated. A threshold distribution with a variance of $\sim 700 e^-$ rms for a setting at 16 500 e^- was obtained. Further threshold measurements are in progress.

Overall detector response

Various measurements were performed with the first detector assemblies using sources. The fast-OR was used in order to increase efficiency of data taking with the randomly incident electrons. The fast-OR

signal with its low voltage swing current logic did not generate any noticeable feedthrough into the sensitive pixel inputs. Fig. 16 shows the scatter plot resulting in a uniform distribution of hits from an irradiation using electrons from a ^{90}Sr source. 10 million events were accumulated with a random trigger.

5. Conclusion

The Omega3/LHC1 pixel readout chip has been bump-bonded to a 300 μm thick Si detector and functionality of most features has been demonstrated. The noise without detector (100 e^- rms) has been estimated by electrical measurements. Threshold is linearly adjustable between $\sim 2\,000\,e^-$ and $15\,000\,e^-$ and threshold non-uniformity has been measured electrically ($\sim 450\,e^-$ rms @ 5000 e^- threshold) and using radioactive sources ($\sim 700\,e^-$ rms @ 16 500 e^- threshold). Timewalk ($< 10\text{ ns}$) and delay precision ($< 6\text{ ns rms}$) have been measured electrically and demonstrate the suitability of the architecture for future LHC applications. The fast-OR circuit works and has been used in radioactive source measurements. Some more advanced features of the chip remain to be tested, in particular the synergy with the COOP control chip, and statistics on various characteristic parameters should be obtained. Practical application of the detectors is foreseen in a new, 8 plane telescope for the WA97 heavy ion experiment in the Omega spectrometer at CERN.

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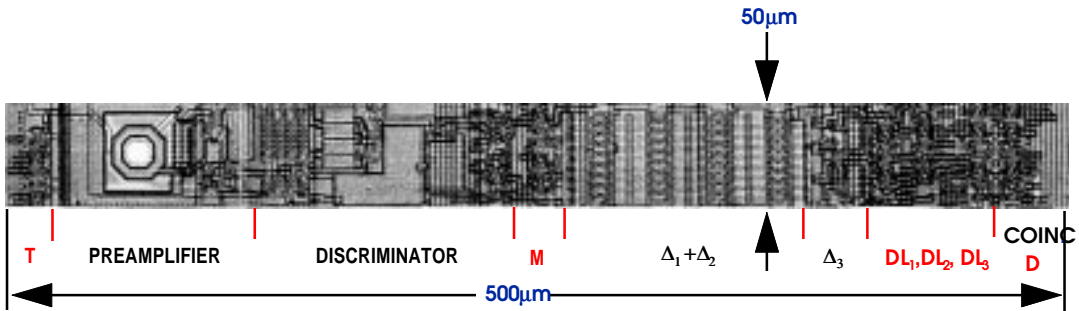


Fig. 1 Design (top) and microphotograph of single pixel cell of the LHC1/Omega3 chip

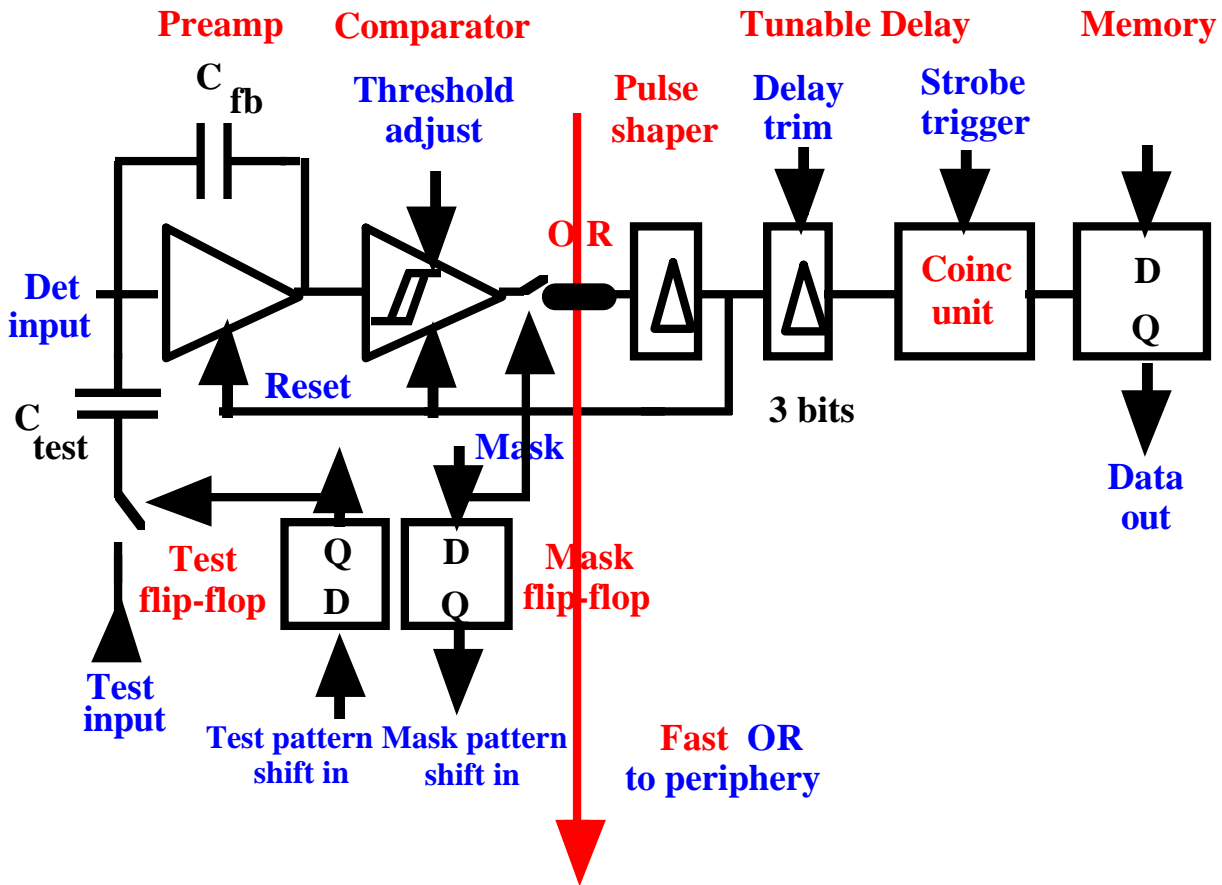


Fig. 2. Block diagram of the pixel cell.

Fig. 4 Photo of the bottom part of a column of cells on the detector chip. The matrix elements have 50 μm height and 500 μm width. One sees the metallizations that cover the diode implantations. An opening of ~ 20 μm for the bump contact is provided through the nearly transparent passivating layer.

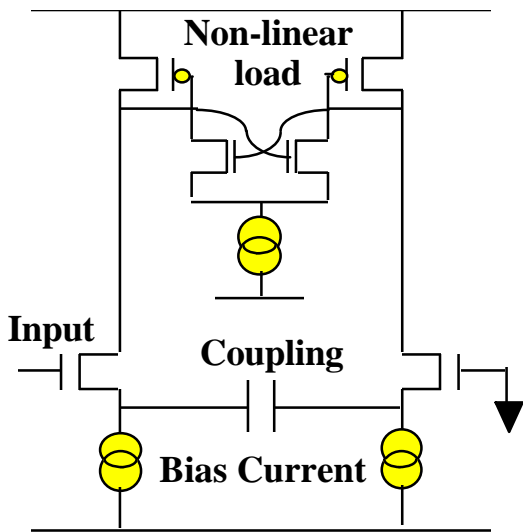


Fig. 5. The comparator contains a bistable non-linear load and is ac coupled to minimize offset effects.

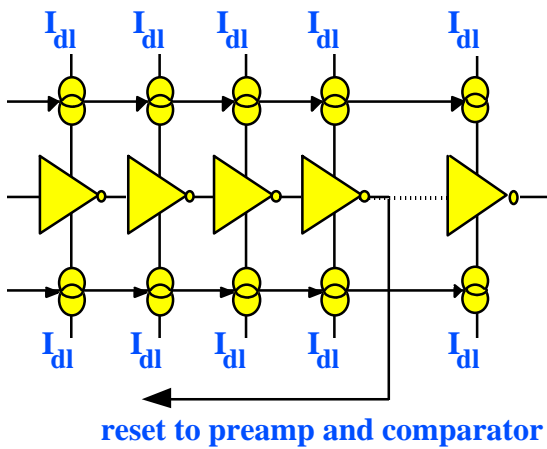


Fig. 6. The main delay chain consist of 36 inverter stages. After the fourth stage the signal is fed back to reset pre amplifier and comparator. The effect of I_{d1} is shown in fig. 11

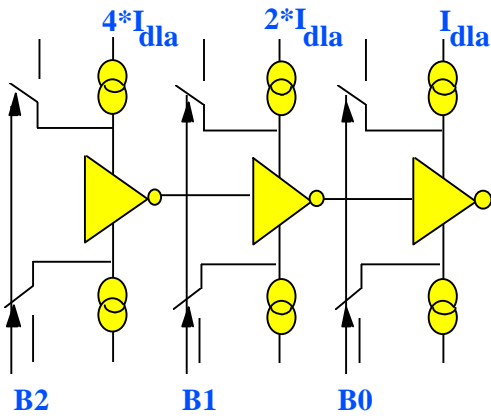


Fig. 7 The 3 bit delay trim is based on inverters which can be made current deprived or not by a switch across the current sources. The I_{dla} can be adjusted externally to set the trimming range between 60 ns and 300 ns.

Fig. 8 Photograph of the LHC1/Omega3 chip. One can distinguish 41 wire bonding pads at the bottom.

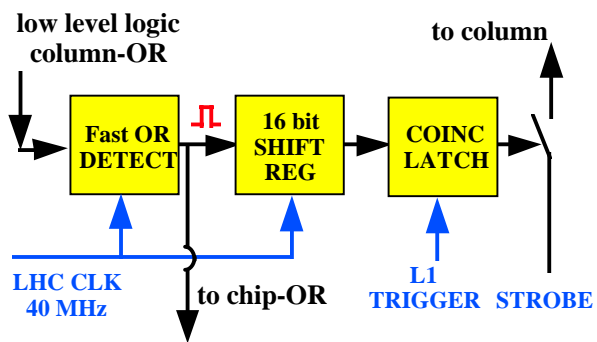


Fig. 9 Circuitry for fast-OR detection and time-stamping of hit columns at the bottom of each column.

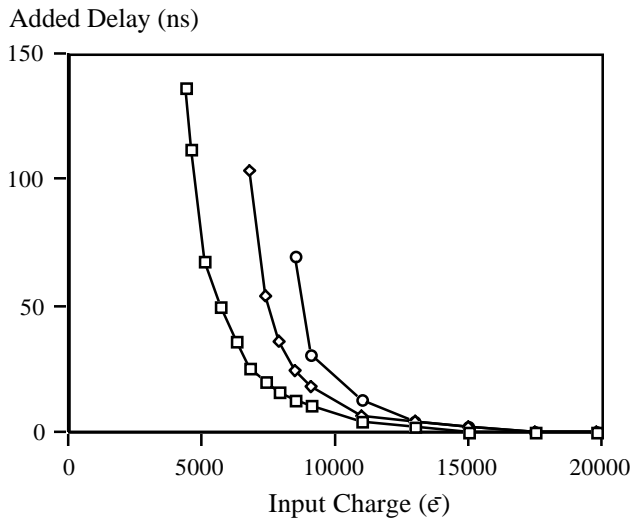


Fig. 10 The added response time of a pixel cell due to timewalk in the discriminator for threshold settings at 5000 e^- , 7000 e^- and 9000 e^- .

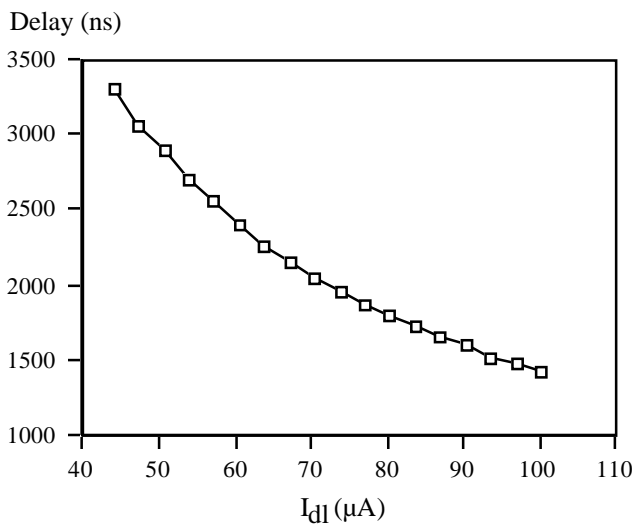


Fig. 11. Adjustment of the internal delay lines of the pixels can be achieved globally by varying the bias current I_{d1} .

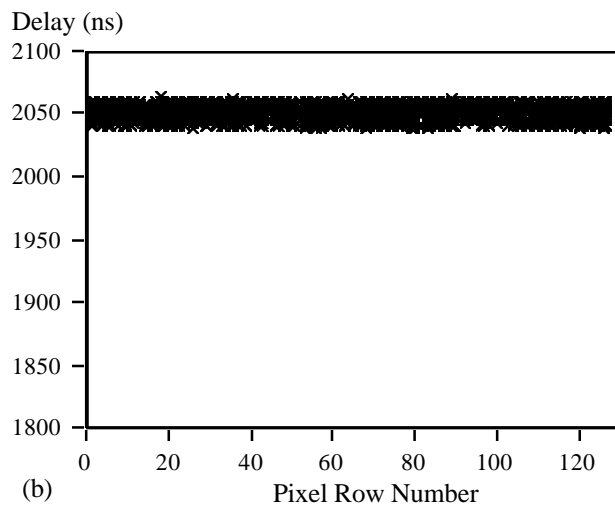
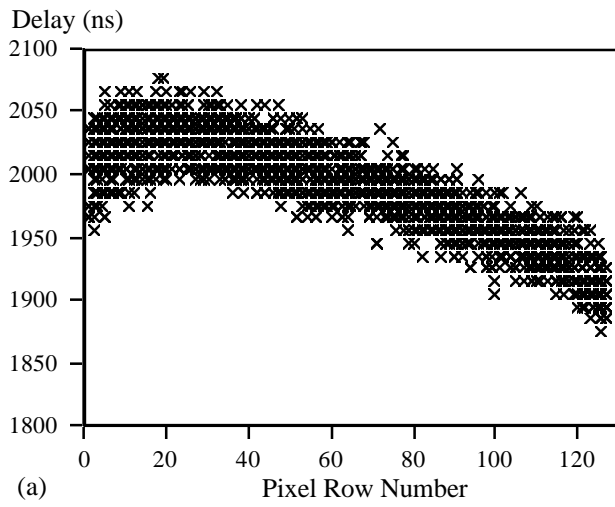


Fig. 12 The time response of 2000 pixels on one chip.

(a) shows the time response before individual pixel delay correction. It indicates a random spread of ~ 100 ns peak-to-peak on top of which are added systematic effects.

(b) indicates that after correction of the delays in each pixel all pixels respond within a 25 ns time window indicating a timing precision of better than 6 ns rms.

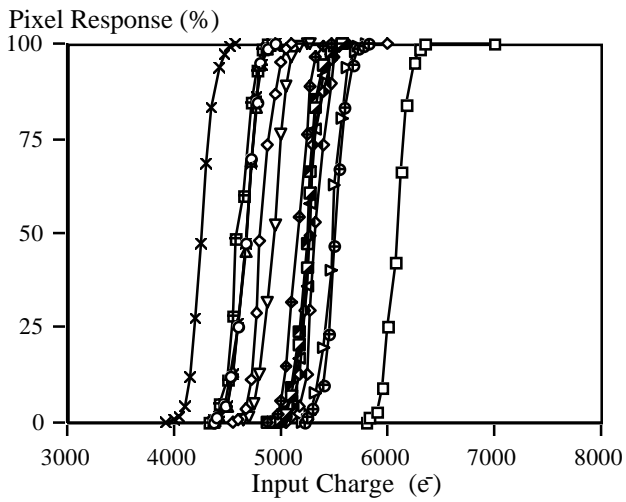


Fig. 13. The proportion of positive responses of pixels in the test rows as a function of input signal height in steps of $50 e^-$ equivalent at a nominal threshold $I_{th} = 10 \mu A$, $\sim 5\,000 e^-$.

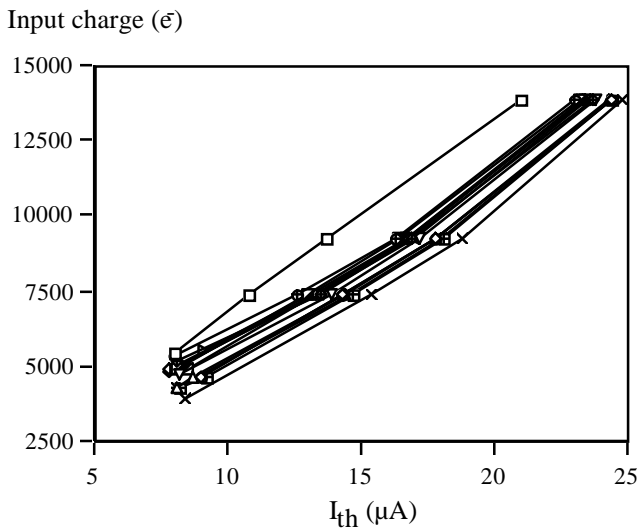


Fig 14. Variation of the threshold plotted against the current I_{th} . It can be noted that there is one channel (ch 0) which behaves differently from the others which may just be incidental. The symbols correspond to those in fig. 13

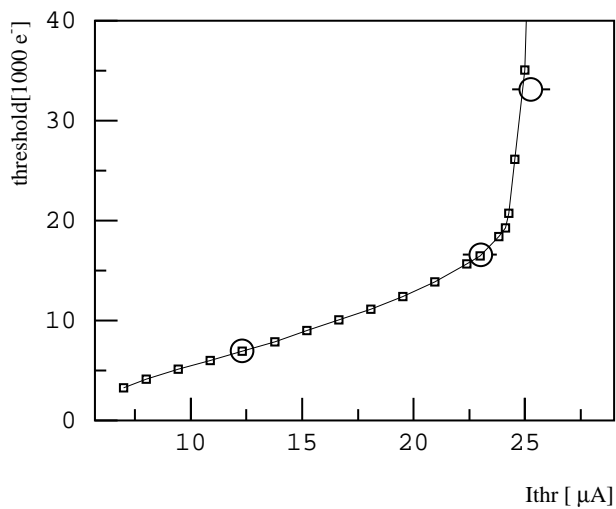


Fig. 15 A calibration of the electrical test measurements on one pixel channel using 3 photon sources (marked with a circle). These were ^{109}Cd (22 keV and 25 keV) ^{241}Am (60 keV) and ^{57}Co (122 keV).

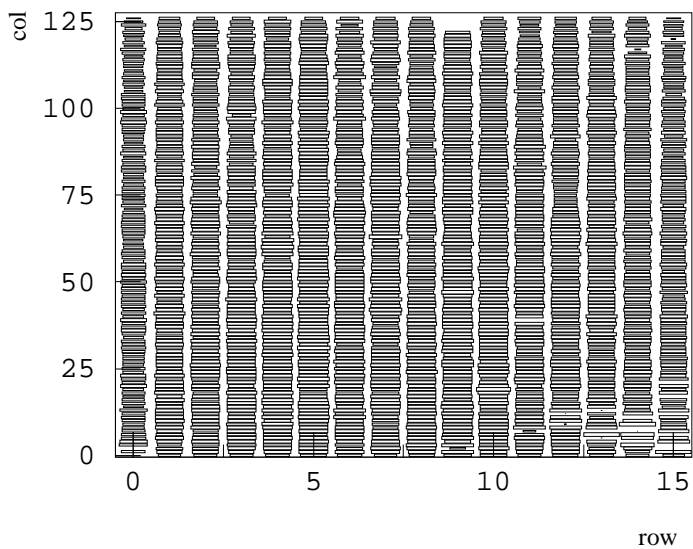


Fig. 16. A scatter plot of hits recorded using a random trigger and a ^{90}Sr source. Each pixel has around 8 000 hits.